# 2SD1750, 2SD1750A

## Silicon NPN triple diffusion planar type darlington

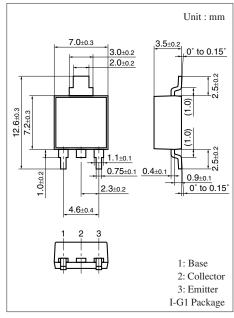
For midium speed power switching Complementary to 2SB1180 and 2SB1180A

#### ■ Features

- High forward current transfer ratio h<sub>FE</sub>
- High-speed switching
- I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment

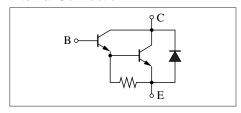
### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SD1750	V <sub>CBO</sub>	60	V
(Emitter open)	2SD1750A		80	
Collector-emitter voltage	2SD1750	V <sub>CEO</sub>	60	V
(Base open)	2SD1750A		80	
Emitter-base voltage (Col	$V_{EBO}$	7	V	
Collector current	$I_{C}$	8	A	
Peak collector current	$I_{CP}$	12	A	
Collector power dissipation	P <sub>C</sub>	15	W	
	$T_a = 25^{\circ}C$		1.3	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



Note) Self-supported type package is also prepared.

#### Internal Connection



### ■ Electrical Characteristics $T_C = 25$ °C $\pm 3$ °C

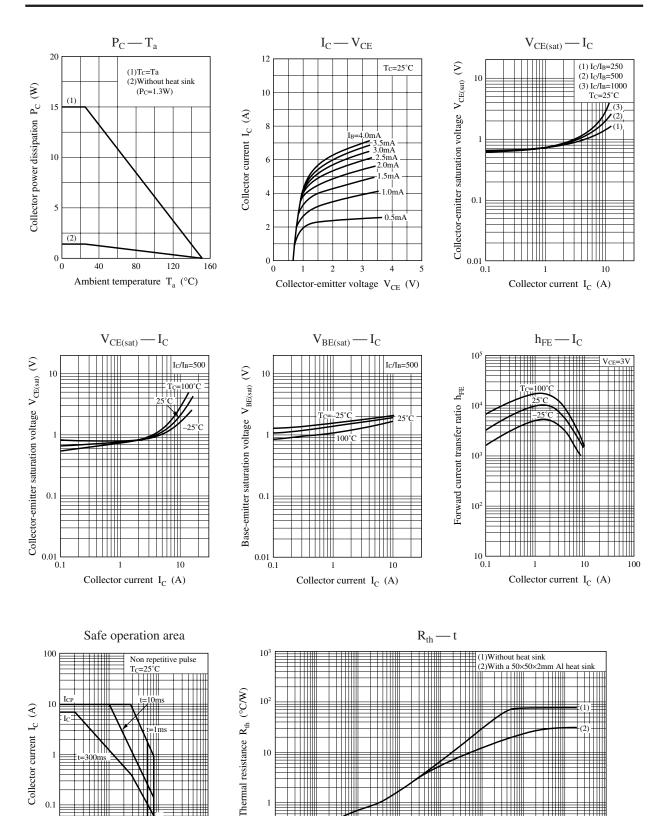
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SD1750	$V_{CEO}$	$I_C = 30 \text{ mA}, I_B = 0$	60			V
(Base open)	2SD1750A			80			
Collector-base cutoff	2SD1750	$I_{CBO}$	$V_{CB} = 60 \text{ V}, I_{E} = 0$			100	μΑ
current (Emitter open)	2SD1750A		$V_{CB} = 80 \text{ V}, I_{E} = 0$			100	
Emitter-base cutoff current (Collector open)		$I_{EBO}$	$V_{EB} = 7 \text{ V}, I_{C} = 0$			2	mA
Forward current transfer ratio		h <sub>FE1</sub> *	$V_{CE} = 3 \text{ V}, I_{C} = 4 \text{ A}$	2000		10 000	_
		h <sub>FE2</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 8 \text{ A}$	500			
Collector-emitter saturation	voltage	V <sub>CE(sat)</sub>	$I_C = 4 \text{ A}, I_B = 8 \text{ mA}$			1.5	V
Base-emitter saturation volt	age	V <sub>BE(sat)</sub>	$I_C = 4 \text{ A}, I_B = 8 \text{ mA}$			2.0	V
Forward current transfer rat	io	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time		t <sub>on</sub>	$I_C = 4 \text{ A}, I_{B1} = 8 \text{ mA}, I_{B2} = -8 \text{ mA}$		0.5		μs
Storage time		t <sub>stg</sub>	$V_{CC} = -50 \text{ V}$		4.0		μs
Fall time		$t_{\rm f}$			1.0		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*: Rank classification

Rank	Q	Р		
$h_{\mathrm{FE}1}$	2000 to 5000	4000 to 10000		

## **Panasonic**



2 SJD00222CED

1000

100

 $10^{-1}$ 

 $10^{-2}$ 

Time t (s)

0.01

10

Collector-emitter voltage  $V_{CE}$  (V)

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